	Type	Hits	Search Text	DBs
1	BRS	185305	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	2815663	sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	149686	inplant or implant or inplanting or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	10	(inplant or implant or inplanting or implanting) near8 (xe or xenon) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	3	((inplant or implant or inplanting or implanting) near8 (xe or xenon) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20021227")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	68	(inplant or implant or inplanting or implanting) same (xe or xenon) same (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	25	((inplant or implant or inplanting or implanting) same (xe or xenon) same (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20021227")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	393	preamorph$8 or pre adj amorph$8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
9	BRS	24	(inplant or implant or inplanting or implanting) near8 (preamorph$8 or pre adj amorph$8) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	16	((inplant or implant or inplanting or implanting) near8 (preamorph$8 or pre adj amorph$8) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad <	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	2103337	ge! or germanium or xe or xenon or ar or argon or silicon or si	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	2411649	ge! or germanium or xe or xenon or ar or argon or silicon or si or inert	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	4743	(inplant or implant or inplanting or implanting) near8 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	1791	((inplant or implant or inplanting or implanting) near8 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20021227")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
15	BRS	725	(inplant or implant or inplanting or implanting) near8 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near8 (through or across or into) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	774	(inplant or implant or inplanting or implanting) near8 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near8 (through or across or into or penetrat$4) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	307	((inplant or implant or inplanting or implanting) near8 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near8 (through or across or into or penetrat$4) near8 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad <"20021227")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	286	(inplant or implant or inplanting or implanting) near4 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near4 (through or across or into or penetrat$4) near4 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
19	BRS	105	((inplant or implant or inplanting or implanting) near4 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near4 (through or across or into or penetrat$4) near4 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20021227")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	16223	(advanced near2 micro).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	98	(((inplant or implant or inplanting or implanting) near4 (ge! or germanium or xe or xenon or ar or argon or silicon or si or inert) near4 (through or across or into or penetrat$4) near4 (sio? or "sio.sub.2" or oxide or insulat$4 or dielectric$4 or nitride or sin)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20021227")) not ((advanced near2 micro).as.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	35	5266510.URPN.	USPAT
23	BRS	13	5650350.URPN.	USPAT
24	BRS	11	("Re29660" | "3895966" | "4422885" | "4928156" | "5045898" | "5134447" | "5266510" | "5362981" | "5396096" | "5407849" | "5448093").PN.	USPAT
25	BRS	3	5879996.URPN.	USPAT
26	BRS	6	("4394181" | "5145794" | "5254484" | "5298435" | "5312766" | "5426069").PN.	USPAT

Type	Hits	Search Text	DBs
27	IS&R	1659	((438/288) or (438/174) or (438/181) or (438/217) or (438/511) or (438/518)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

04/30/2004, EAST Version: 1.4.1